

Substitute for form 1449/PTO

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

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Application Number	10/525,297
Filing Date	02/15/2005
Inventor(s)	James S. Im
Art Unit	2822
Examiner Name	Bac H. Au
Attorney Docket Number	070050.2717

U.S. PATENT DOCUMENTS

Exam Initial	No.	Document No.	Publication Date	Applicant(s)
	1.	4514895	5/7/1985	Nishimura, Tadashi
	2.	4976809	12/11/1990	Broadbent, Eliot K.
	3.	5417897	5/23/1995	Asakawa, Stuart D. ; McClelland, Paul H. ; Tappon, Ellen R. ; Vandepoll, Richard R. ; Trueba, Kenneth E. ; Chen, Chien Hua
	4.	5436095	7/25/1995	Mizuno, Fumio ; Moriuchi, Noboru ; Shirai, Seiichiro ; Morita, Masayuki
	5.	5466908	11/14/1995	Hosoya, Kimio ; Teruya, Yoshihiro ; Kobayashi, Yasushi
	6.	5512494	4/30/1996	Tanabe, Hiroshi
	7.	5614421	3/25/1997	Yang, Sheng Hsing
	8.	5614426	3/25/1997	Funada, Fumiaki ; Morita, Tatsuo ; Tanaka, Hirohisa ; Zhang, Hongyong ; Takayama, Toru
	9.	5616506	4/1/1997	Takemura, Yasuhiko
	10.	5620910	4/15/1997	Teramoto, Satoshi
	11.	5710050	1/20/1998	Makita, Naoki ; Miyamoto, Tadayoshi
	12.	5736709	4/7/1998	Neiheisel, Gary L.

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	13.	6093934	7/25/2000	Yamazaki, Shunpei ; Teramoto, Satoshi ; Koyama, Jun ; Ogata, Yasushi ; Hayakawa, Masahiko ; Osame, Mitsuaki ; Ohtani, Hisashi ; Hamatani, Toshiji
	14.	6117301	9/12/2000	Freudenberger, Renate ; Zielonka, Andreas
	15.	6198141	3/6/2001	Yamazaki, Shunpei ; Ohtani, Hisashi ; Fukunaga, Takeshi
	16.	6222195	4/24/2001	Yamada, Akio ; Sagou, Satoru ; Watanabe, Hitoshi ; Yamazaki, Satoru ; Sakamoto, Kiichi ; Ohno, Manabu ; Kawakami, Kenichi ; Kobayashi, Katsuhiko
	17.	6255146	7/3/2001	Shimizu, Satoshi ; Ueno, Shuichi ; Maeda, Shigenobu ; Ipposhi, Takashi
	18.	6274488	8/14/2001	Talwar, Somit ; Wang, Yun
	19.	6341042	1/22/2002	Matsunaka, Shigeki ; Fujihara, Atsushi ; Kakuno, Tsutomu
	20.	6348990	2/19/2002	Igasaki, Yasunori ; Yoshida, Narihiro ; Toyoda, Haruyoshi ; Hara, Tsutomu
	21.	6353218	3/5/2002	Yamazaki, Shunpei ; Tanaka, Koichiro
	22.	6358784	3/19/2002	Zhang, Hongyong ; Yamazaki, Shunpei ; Takemura, Yasuhiko
	23.	6388386	5/14/2002	Kunii, Masafumi ; Takatoku, Makoto ; Mano, Michio

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	24.	6392810	5/21/2002	Tanaka, Koichiro
	25.	6393042	5/21/2002	Tanaka, Koichiro
	26.	6410373	6/25/2002	Chang, Ting Chang ; Zan, Hsiao Wen ; Shih, Po Sheng
	27.	20020083557	7/4/2002	Jung, Yun Ho
	28.	6429100	8/6/2002	Yoneda, Kiyoshi
	29.	6432758	8/13/2002	Cheng, Huang Chung ; Lin, Ching Wei ; Cheng, Li Jing
	30.	20020119609	8/29/2002	Hatano, Mutsuko ; Yamaguchi, Shinya ; Kimura, Yoshinobu ; Park, Seong Kee
	31.	6445359	9/3/2002	Ho, Kesse
	32.	6448612	9/10/2002	Miyazaki, Minoru ; Murakami, Akane ; Cui, Baochun ; Yamamoto, Mutsuo
	33.	6451631	9/17/2002	Grigoropoulos, Costas P. ; Hatano, Mutsuko ; Lee, Ming Hong ; Moon, Seung Jae
	34.	6455359	9/24/2002	Yamazaki, Shunpei ; Teramoto, Satoshi ; Kusumoto, Naoto ; Fukunaga, Takeshi ; Nakajima, Setsuo ; Miyamoto, Tadayoshi ; Yoshinouchi, Atsushi
	35.	20020151115	10/17/2002	Nakajima, Hideharu ; Negoro, Yoichi ; Usui, Setsuo
	36.	6471772	10/29/2002	Tanaka, Koichiro

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	37.	6472684	10/29/2002	Yamazaki, Shunpei ; Koyama, Jun ; Hayashi, Keisuke
	38.	6476447	11/5/2002	Yamazaki, Shunpei ; Mase, Akira ; Hiroki, Masaaki ; Takemura, Yasuhiko ; Zhang, Hongyong ; Uochi, Hideki
	39.	6482722	11/19/2002	Kunii, Masafumi ; Takatoku, Makoto ; Mano, Michio
	40.	6493042	12/10/2002	Bozdagi, Gozde ; Yu, Hong Heather ; Harrington, Steven J. ; Bryll, Robert
	41.	6495405	12/17/2002	Voutsas, Apostolos ; Hartzell, John W. ; Nakata, Yukihiko
	42.	6501095	12/31/2002	Yamaguchi, Shinya ; Hatano, Mutsuko ; Shiba, Takeo ; Kimura, Yoshinobu ; Park, Seong Kee
	43.	20030000455	1/2/2003	Voutsas, Apostolos
	44.	20030006221	1/9/2003	Hong, Minghui ; Ye, Kaidong ; An, Chengwu ; Liu, Da Ming
	45.	6506636	1/14/2003	Yamazaki, Shunpei ; Asami, Taketomi ; Ichijo, Mitsuhiko ; Mitsuki, Toru ; Kanakubo, Yoko
	46.	20030013278	1/16/2003	Jang, Jin ; Kim, Kyung, Ho
	47.	20030014337	1/16/2003	Mathews, Scott, H. ; Datar, Vinay, T.
	48.	6512634	1/28/2003	Tanaka, Koichiro

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	49.	6516009	2/4/2003	Tanaka, Koichiro
	50.	6521473	2/18/2003	Jung, Yun Ho
	51.	6535535	3/18/2003	Yamazaki, Shunpei ; Tanaka, Koichiro
	52.	20030068836	4/10/2003	Hongo, Mikio ; Uto, Sachio ; Nomoto, Mineo ; Nakata, Toshihiko ; Hatano, Mutsuko ; Yamaguchi, Shinya ; Ohkura, Makoto
	53.	6562701	5/13/2003	Ishida, Masahiro ; Ueda, Daisuke ; Yuri, Masaaki
	54.	6563077	5/13/2003	Im, James S.
	55.	20030089907	5/15/2003	Yamaguchi, Shinya ; Hatano, Mutsuko ; Shiba, Takeo
	56.	6573163	6/3/2003	Voutsas, Apostolos ; Hartzell, John W. ; Nakata, Yukihiko
	57.	6577380	6/10/2003	Sposili, Robert S. ; Farmiga, Nestor O. ; Jain, Kanti
	58.	20030119286	6/26/2003	Im, James, S. ; Sposili, Robert, S. ; Crowder, Mark, A.
	59.	6590228	7/8/2003	Voutsas, Apostolos ; Hartzell, John W. ; Nakata, Yukihiko
	60.	20030148565	8/7/2003	Yamanaka, Hideo
	61.	6608326	8/19/2003	Shinagawa, Youmei ; Mimura, Akio ; Kawachi, Genshiro ; Satoh, Takeshi

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	62.	20030194613	10/16/2003	Voutsas, Apostolos, T. ; Crowder, Mark, A. ; Mitiani, Yasuhiro
	63.	6635932	10/21/2003	Grigoropoulos, Costas P. ; Hatano, Mutsuko ; Lee, Ming Hong ; Moon, Seung Jae
	64.	6660575	12/9/2003	Zhang, Hongyong
	65.	6667198	12/23/2003	Shimoto, Shigeyuki ; Uchikoga, Shuichi
	66.	6693258	2/17/2004	Sugano, Yukiyasu ; Fujino, Masahiro ; Mano, Michio ; Asano, Akihiko ; Ino, Masumitsu ; Urazono, Takenobu ; Takatoku, Makoto
	67.	6734635	5/11/2004	Kunii, Masafumi ; Takatoku, Makoto ; Mano, Michio
	68.	20040127066	7/1/2004	Jung, Yun Ho
	69.	20040140470	7/22/2004	Kawasaki, Ritsuko ; Kasahara, Kenji ; Ohtani, Hisashi
	70.	6767804	7/27/2004	Crowder, Mark Albert
	71.	6770545	8/3/2004	Yang, Myoung Su
	72.	6784455	8/31/2004	Maekawa, Masashi ; Nakata, Yukihiro
	73.	20040169176	9/2/2004	Peterson, Paul, E. ; Stasiak, James
	74.	20040182838	9/23/2004	Das, Palash, P. ; Bolliger, Bruce, E. ; Patel, Parthiv, S. ; Klene, Brian, C. ; Melcher, Paul, C. ; Saethre, Robert, B.

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	75.	20040222187	11/11/2004	Lin, Kun Chih
	76.	20040224487	11/11/2004	Yang, Myoung Su
	77.	6858477	2/22/2005	Deane, Steven C. ; French, Ian D.
	78.	20050059265	3/17/2005	Im, James
	79.	6908835	6/21/2005	Sposili, Robert S. ; Im, James S.
	80.	20050141580	6/30/2005	Partlo, William ; Das, Palash ; Hudyma, Russell ; Thomas, Michael
	81.	20050142450	6/30/2005	Jung, Yun
	82.	20050142451	6/30/2005	You, JaeSung
	83.	20050202654	9/15/2005	Im, James
	84.	6961117	11/1/2005	Im, James S.
	85.	20060030164	2/9/2006	Im, James
	86.	20060102901	5/18/2006	Im, James ; van der Wilt, Paul
	87.	20060125741	6/15/2006	Tanaka, Masahiro ; Matsuura, Toshiyuki ; Murakami, Hajime ; Akimoto, Hajime
	88.	7091411	8/15/2006	Falk, Fritz ; Andrae, Gudrun
	89.	20060211183	9/21/2006	Duan, Xiangfeng ; Niu, Chunming ; Empedocles, Stephen ; Romano, Linda ; Chen, Jian ; Sahi, Vijendra ; Bock, Lawrence ; Stumbo, David ; Parce, J. ; Goldman, Jay

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	90.	20060254500	11/16/2006	Im, James ; Van Der Wilt, Paul
	91.	20070007242	1/11/2007	Im, James
	92.	20070020942	1/25/2007	Im, James
	93.	20070032096	2/8/2007	Im, James, S.
	94.	7187016	3/6/2007	Arima, Yutaka
	95.	7217605	5/15/2007	Kawasaki, Ritsuko ; Nakajima, Setsuo
	96.	20070108472	5/17/2007	Jeong, Jac, Kyeong ; Shin, Hyun, Soo ; Kwon, Se, Yeoul ; Mo, Yeon, Gon
	97.	20070111349	5/17/2007	Im, James
	98.	7259081	8/21/2007	Im, James S.
	99.	20070215942	9/20/2007	Chen, Po Chu ; Ho, King Yuan
	100.	7297982	11/20/2007	Suzuki, Kenkichi ; Nagata, Tetsuya ; Takahashi, Michiko ; Saito, Masakazu ; Ogino, Toshio ; Miyano, Masanobu
	101.	7300858	11/27/2007	Im, James S.
	102.	7311778	12/25/2007	Im, James S. ; van der Wilt, Paul Christiaan
	103.	7341928	3/11/2008	Im, James S.

FOREIGN PATENT DOCUMENTS

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	104.	DE10103670 (with English machine translation)	8/1/2002	Christiansen, Jens Ingwer, Prof. Dr. ; Christiansen, Silke, Dr. ; Strunk, Horst Paul, Prof. Dr. ; Otto, Andreas, Dipl.-Phys. Dr.-Ing. ; Eßer, Gerd, Dipl.-Ing. ; Urmoneit, Uwe, Dipl.-Phys.
	105.	DE19839718 (with English machine translation)	3/2/2000	Christiansen, Jens Ingwer, Prof. Dr. ; Christiansen, Kai, Dipl.-Phys. ; Christiansen, Silke, Dr. ; Ngendanc, Matthias, Dipl.-Phys. ; Strunk, Horst Paul, Prof. Dr.
	106.	JP4279064 (with English Abstract)	10/5/1992	UEDA TORU
	107.	JP11281997 (with English machine translation)	10/15/1999	GOTO YASUMASA ; IMAI NOBUO
	108.	WO01071791	9/27/2001	IM, James, S. ; SPOSILI, Robert, S. ; CROWDER, Mark, A.
	109.	WO05029546	3/31/2005	IM, James, S.
	110.	WO05029548	3/31/2005	IM, James, S.
	111.	WO05029550	3/31/2005	IM, James, S.
	112.	WO05029551	3/31/2005	IM, James, S. ; VAN DER WILT, Paul, Christiaan

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113.	BERGMANN, R. et al., Nucleation and Growth of Crystalline Silicon Films on Glass for Solar Cells, Phys. Stat. Sol., 1998, pp. 587-602, Vol. 166, Germany.
114.	BIEGELSEN, D.K., L.E. Fennell and J.C. Zesch, Origin of oriented crystal growth of radiantly melted silicon on SiO ₂ /sub 2, Appl. Phys. Lett. 45, 546 (1984).
115.	Boyd, Laser Processing of Thin Films and Microstructures, Oxidation, Deposition, and Etching of Insulators (Springer--Verlag Berlin Heidelberg 1987).
116.	BROTHERTON, S.D., et al., Characterisation of poly-Si TFTs in Directionally Solidified SLS Si, Asia Display/IDS'01, p. 387-390.
117.	Crowder et al., "Parametric investigation of SLS-processed poly-silicon thin films for TFT application," Preparations and Characterization, Elsevier, Sequoia, NL, vol. 427, no. 1-2, 3 March 2003, pages 101-107, XP004417451.
118.	CROWDER et al., "Sequential Lateral Solidification of PECVD and Sputter Deposited a-Si Films", Mat. Res. Soc. Symp. Proc. 621:Q.9.7.1-9.7.6, 2000.
119.	DASSOW, R. et al. Laser-Crystallized Polycrystalline Silicon on Glass for Photovoltaic Applications, Solid State Phenomena, pp. 193-198, Vols. 67-68, Scitec Publications, Switzerland.
120.	DASSOW, R. et al. Nd:YVO ₄ Laser Crystallization for Thin Film Transistors with a High Mobility, Mat. Res. Soc. Symp. Proc., 2000, Q9.3.1-Q9.3.6, Vol. 621, Materials Research Society.
121.	DASSOW, R. et al., Laser crystallization of silicon for high-performance thin-film transistors, Semicond. Sci. Technol., 2000, pp. L31-L34, Vol. 15, UK.
122.	DIMITRIADIS, C.A., J. Stoemenos, P.A. Coxon, S. Friligkos, J. Antonopoulos and N.A. Economou, Effect of pressure on the growth of crystallites of low-pressure chemical-vapor-deposited polycrystalline silicon films and the effective electron mobility under high normal field in thin-film transistors, J. Appl. Phys. 73, 8402 (1993).

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123.	GEIS et al., "Crystallographic orientation of silicon on an amorphous substrate using an artificial surface-relief grating and laser crystallization," Appl. Phys. Lett. 35(1) July 1, 1979, 71-74.
124.	GEIS et al., "Silicon graphoeptaxy using a strip-heater oven," Appl. Phys. Lett. 37(5), September 1, 1980, 454-456.
125.	Geis et al., "Zone-Melting recrystallization of SI Films with a moveable-strip heater oven" J. Electro-Chem. Soc., 129; 2812 (1982).
126.	GUPTA et al., "Numerical Analysis of Excimer-laser induced melting and solidification of Si Thin Films", Applied Phys. Lett., 71:99, 1997.
127.	Hau-Reige et al., "Microstructural Evolution Induced By Scanned Laser Annealing in Al Interconnects," Appl. Phys. Lett., vol. 75, No. 10, p. 1464-1466, 1999
128.	HAWKINS, W.G. et al., "Origin of lamellae in radiatively melted silicon films," appl. Phys. Lett. 42(4), 15 February 1983.
129.	HAYZELDEN, C. and J.L. Batstone, Silicide formation and silicide-mediated crystallization of nickel-implanted amorphous silicon thin films, J. Appl. Phys. 73, 8279 (1993).
130.	IM, J.S., Method and system for producing crystalline thin films with a uniform crystalline orientation, application # 60/503419; ref. file # 36013(BB); Columbia ref. M02-063.
131.	JUNG, Y.H., et al., Low Temperature Polycrystalline Si TFTs Fabricated with Directionally Crystallized Si Film, Mat. Res. Soc. Symp. Proc. Vol. 621, Z8.3.1-6, 2000.
132.	JUNG, Y.H., et al., The Dependence of Poly-Si TFT Characteristics on the Relative Misorientation Between Grain Boundaries and the Active Channel, Mat. Res. Soc. Symp. Proc. Vol. 621, Q9.14.1-6, 2000.
133.	KAHLERT, H., "Creating Crystals", OE Magazine, November 2001, 33-35.
134.	KIM, C. et al., Development of SLS-Based SOG Display, IDMC 2005, Thu-15-02, 252-255.

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-----------------------	--	--------------------	--

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135.	KIM, H. J. et al., "Excimer Laser Induced Crystallization of Thin Amorphous Si Films on SiO ₂ : Implications of Crystallized Microstructures for Phase Transformation Mechanisms," Mat. Res. Soc. Symp. Proc., Vol. 283, 1993.
136.	KIM, H.J. et al., "New Excimer-laser-crystallization method for producing large-grained and grain boundary-location-controlled Si Films for Thin Film Transistors", Applied Phys. Lett., 68: 1513.
137.	KIM, H.J. et al., "Multiple Pulse Irradiation Effects in Excimer Laser-Induced Crystallization of Amorphous Si Films," Mat. Res. Soc. Sym. Proc., 321:665-670 (1994).
138.	Kim, H.-J., et al., "The effects of dopants on surface-energy-driven secondary grain growth in silicon films," J. Appl. Phys. 67 (2), 15 January 1990.
139.	KIMURA, M. and K. Egami, Influence of as-deposited film structure on (100) texture in laser-recrystallized silicon on fused quartz, Appl. Phys. Lett. 44, 420 (1984).
140.	KNOWLES, D.S. et al., "P-59: Thin Beam Crystallization Method: a New Laser Annealing Tool with Lower Cost and Higher Yield for LTPS Panels," SID 00 Digest, pp. 1-3
141.	KOHLER, J.R. et al., Large-grained polycrystalline silicon on glass by copper vapor laser annealing. Thin Solid Films, 1999, pp. 129-132, Vol. 337, Elsevier.
142.	KUNG, K.T.Y. and R. Reif, Implant-dose dependence of grain size and (110) texture enhancements in polycrystalline Si films by seed selection through ion channeling, J. Appl. Phys. 59, 2422 (1986).
143.	KUNG, K.T.Y., R.B. Iverson and R. Reif, Seed selection through ion channeling to modify crystallographic orientations of polycrystalline Si films on SiO ₂ /sub 2: Implant angle dependence, Appl. Phys. Lett. 46, 683 (1985).
144.	KURIYAMA, H., T. Nohda, S. Ishida, T. Kuwahara, S. Noguchi, S. Kiyama, S. Tsuda and S. Nakano, Lateral grain growth of poly-Si films with a specific orientation by an excimer laser annealing method, Jpn. J. Appl. Phys. 32, 6190 (1993).

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Filing Date	02/15/2005
Inventor(s)	James S. Im
Art Unit	2822
Examiner Name	Bac H. Au
Attorney Docket Number	070050.2717

145.	KURIYAMA, H., T. Nohda, Y. Aya, T. Kuwahara, K. Wakisaka, S. Kiyama and S. Tsuda, Comprehensive study of lateral grain growth in poly-Si films by excimer laser annealing and its application to thin film transistors, Jpn. J. Appl. Phys. 33 , 5657 (1994).
146.	LEE, S.-W. and S.-K. Joo, Low temperature poly-Si thin-film transistor fabrication by metal-induced lateral crystallization, IEEE Electron Device Letters 17 , 160 (1996).
147.	LEE, S.-W., Y.-C. Jeon and S.-K. Joo, Pd induced lateral crystallization of amorphous Si thin films, Appl. Phys. Lett. 66 , 1671 (1995).
148.	LEONARD, J.P. et al, "Stochastic modeling of solid nucleation in supercooled liquids", Appl. Phys. Lett. 78 :22, May 28, 2001, 3454-3456.
149.	LIMANOV, A. et al., Single-Axis Projection Scheme for Conducting Sequential Lateral Solidification of Si Films for Large-Area Electronics, Mat. Res. Soc. Symp. Proc., 2001, D10.1.1-D10.1.7, Vol. 685E, Materials Research Society.
150.	LIMANOV, A. et al., The Study of Silicon Films Obtained by Sequential Lateral Solidification by Means of a 3-k-Hz Excimer Laser with a Sheetlike Beam, Russian Microelectronics, 1999, pp. 30-39, Vol. 28, No. 1, Russia.
151.	LIMANOV, A.B., et al., Development of Linear Sequential Lateral Solidification Technique to Fabricate Quasi-Single-Crystal Super-thin Si Films for High-Performance Thin Film Transistor Devices, Perspectives, Science, and Technologies for Novel Silicon on
152.	Mariucci et al., "Advanced excimer laser crystallization techniques," Thin Solid Films, vol. 338, pp. 39-44, 2001
153.	Micro/Las Lasersystem, GmbH, "UV Optics Systems for Excimer Laser Based Micromachining and Marking" (1999).
154.	MIYASAKA, M., K. Makihiro, T. Asano, E. Polychroniadis and J. Stoemenos, In situ observation of nickel metal-induced lateral crystallization of amorphous silicon thin films, Appl. Phys. Lett. 80 , 944 (2002).

Examiner Signature	Date Considered
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NY02:659899.2

* Examiner: Initial citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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155.	NERDING, M., S. Christiansen, R. Dassow, K. Taretto, J.R. Kohler and H.P. Strunk, Tailoring texture in laser crystallization of silicon thin-films on glass, Solid State Phenom. 93 , 173 (2003).
156.	Sato et al., "Mobility anisotropy of electrons in inversion layers on oxidized silicon surfaces" Physical Review B (State State) 4 , 1950 (1971)
157.	SMITH, H.I. et al., "The Mechanism of Orientation in Si Graphoepitaxy by Laser or Strip Heater Recrystallization," J. Electrochem. Soc.: Solid-State Science and Technology," Taiwan FPD, June 11, 2005, pp. 1-12
158.	SONG et al., "Single Crystal Si Islands on SiO ₂ Obtained Via Excimer Laser Irradiation of a Patterned Si Film", Applied Phys. Lett., 68 :3165, 1996.
159.	SPOSILI et al., "Line-scan sequential lateral solidification of Si thin films", Appl. Phys. A67 , 273-6, 1998.
160.	THOMPSON, C.V. and H.I. Smith, Surface-energy-driven secondary grain growth in ultrathin (<100 nm) films of silicon, Appl. Phys. Lett. 44 , 603 (1984).
161.	VAN DER WILT, P.C., "Textured poly-Si films for hybrid SLS," July 2004, pp. 1-5
162.	VAN DER WILT, P.C., "State-of-the-Art Laser Crystallization of Si for Flat Panel Displays," PhAST, May 18, 2004, pp. 1-34
163.	Voutsas, A. T., "Assessment of the Performance of Laser-Based Lateral-Crystallization Technology via Analysis and Modeling of Polysilicon Thin-Film-Transistor Mobility," IEEE Transactions on Electronic Devices, Vol. 50, No. 6, June 2003.
164.	VOUTSAS, A.T., A new era of crystallization: advances in polysilicon crystallization and crystal engineering, Applied Surface Science 250-262 , 2003.
165.	VOUTSAS, A.T., et al., Effect of process parameters on the structural characteristics of laterally grown, laser-annealed polycrystalline silicon films, Journal of Applied Physics, Vol. 94 , No. 12, p. 7445-7452, December 15, 2003.

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166.	WEINER, K. H. et al. "Laser-assisted, Self-aligned Silicide Formation," A Verdant Technologies technical brief, August 7, 1997, 1-9.
167.	WERNER, J.H., et al. From polycrystalline to single crystalline silicon on glass, Thin Solid Films 383, 95-100, 2001.
168.	White et al., "Characterization of thin-oxide MNOS memory transistors" IEEE Trans. Electron Devices ED-19, 1280 (1972).

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Considered

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